

# N-Channel 40-V (D-S) MOSFET

## **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

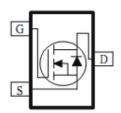
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- Power Routing
- Li Ion Battery Packs
- Level Shifting and Driver Circuits

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)	
40	26 @ V <sub>GS</sub> = 10V	5.8	
	35 @ V <sub>GS</sub> = 4.5V	5.0	







ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage		$V_{DS}$	40	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
O-retirence Dunin Comment 8	T <sub>A</sub> =25°C		5.8		
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =70°C	l <sub>D</sub>	4.6	Α	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	30		
Continuous Source Current (Diode Conduction) a		Is	2.1	Α	
Decree Dissipation 8	T <sub>A</sub> =25°C	P <sub>D</sub>	1.3	W	
Power Dissipation <sup>a</sup>	T <sub>A</sub> =70°C	<b>'</b> 'D	0.8	٧٧	
Operating Junction and Storage Temperature Range		$T_J, T_{sta}$	-55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter			Maximum	Units	
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	100	°C/W	
Maximum Junction-to-Ambient	Steady State	IΛθΊΑ	166	C/VV	

#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

# MI2344N

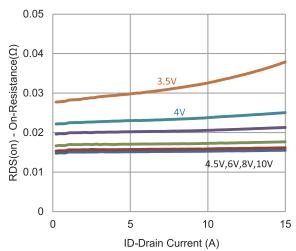
## **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zoro Coto Voltogo Drain Current		$V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Drain Current	DSS	$V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10		
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	9			Α	
Drain Source On Registence a	r	$V_{GS} = 10 \text{ V}, I_D = 4.6 \text{ A}$			26	mΩ	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_{D} = 3.7 \text{ A}$			35	11122	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 4.6 \text{ A}$		8		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 1.1 \text{ A}, V_{GS} = 0 \text{ V}$		0.74		V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_g$	$V_{DS} = 20 \text{ V}, V_{GS} = 4.5 \text{ V},$		9.9		nC	
Gate-Source Charge	$Q_{gs}$	$I_{DS} = 20 \text{ V}, V_{GS} = 4.3 \text{ V},$ $I_{D} = 4.6 \text{ A}$		2.9			
Gate-Drain Charge	$Q_{gd}$	1D - 4.0 A		3.7			
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = 20 \text{ V}, R_{L} = 4.4 \Omega,$		8			
Rise Time	t <sub>r</sub>	$V_{DS} = 20 \text{ V}, R_L = 4.4 \Omega,$ $I_D = 4.6 \text{ A},$ $V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		5		ne	
Turn-Off Delay Time	$t_{d(off)}$			32		ns	
Fall Time	t <sub>f</sub>	V GEN - 10 V, 1 (GEN - 0 12		8			
Input Capacitance	C <sub>iss</sub>			1581			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		121		рF	
Reverse Transfer Capacitance	C <sub>rss</sub>			111			

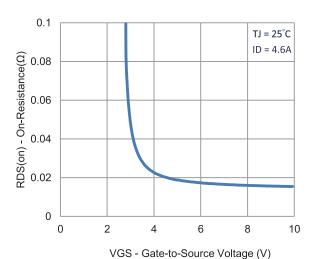
### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

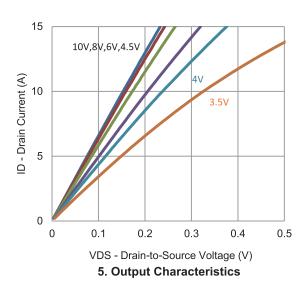
## **Typical Electrical Characteristics**

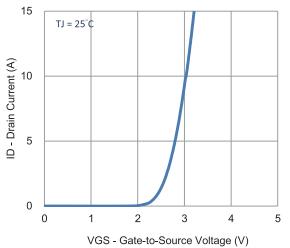


#### 1. On-Resistance vs. Drain Current

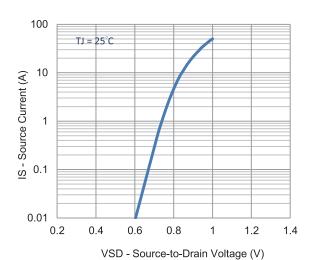


3. On-Resistance vs. Gate-to-Source Voltage

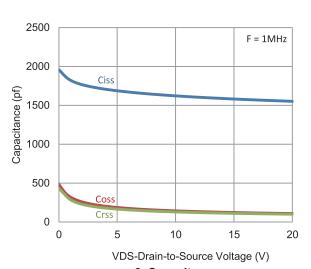




2. Transfer Characteristics

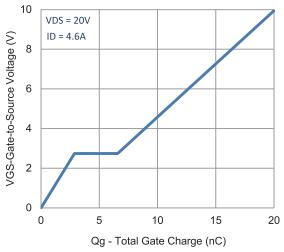


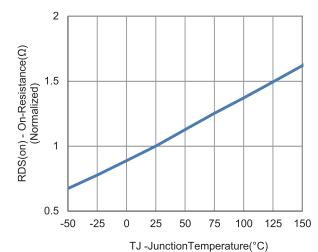
4. Drain-to-Source Forward Voltage



6. Capacitance

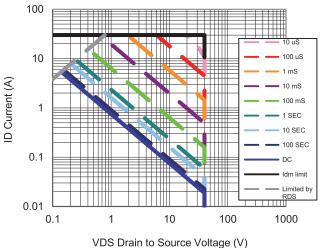


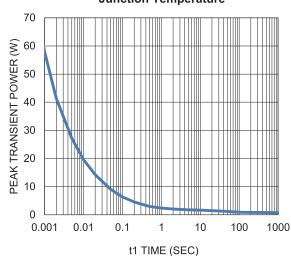




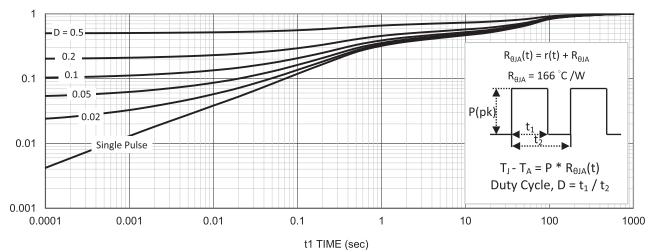
7. Gate Charge 8. Normalized On-Resistance Vs

Junction Temperature



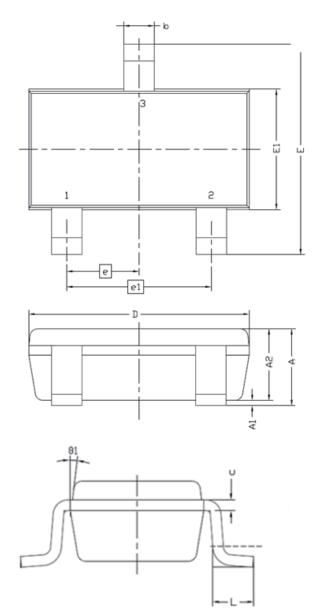


9. Safe Operating Area 10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

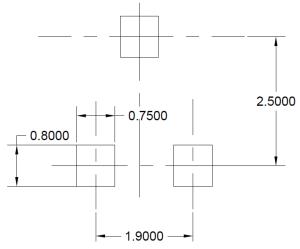
## **Package Information**



Symbol	MILLIMETERS		
Symbol	MIN	MAX	
А	8.0	1.2	
A1	0	0.1	
A2	0.7	1.1	
b	0.3	0.5	
С	0.1	0.2	
D	2.7	3.1	
E	2.6	3	
E1	1.4	1.8	
е	0.95 BSC		
e1	1.9 BSC		
Ĺ	0.3	0.6	
θ1	7° NOM		

## **Recommended Pad Layout**

Note: Drain opening is recommended to be solder mask defined in a copper fill to provide improved thermal performance



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